2SA1806J

Silicon PNP epitaxial planar type

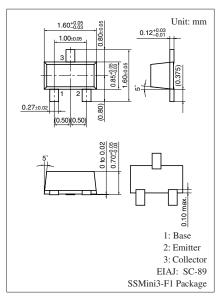
For high speed switching

■ Features

- High speed switching
- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | -15 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | -15 | V | |
| Emitter-base voltage (Collector open) | V_{EBO} | -4 | V | |
| Collector current | I_C | -50 | mA | |
| Peak collector current | I_{CP} | -100 | mA | |
| Collector power dissipation | P _C | 125 | mW | |
| Junction temperature | T_j | 125 | °C | |
| Storage temperature | T_{stg} | -55 to +125 | °C | |



Marking Symbol: AK

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|--|-----|-------|-------|------|
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = -8 \text{ V}, I_E = 0$ | | | - 0.1 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{CE} = -3 \text{ V}, I_C = 0$ | | | - 0.1 | μΑ |
| Forward current transfer ratio | h _{FE1} * | $V_{CE} = -1 \text{ V}, \ I_{C} = -10 \text{ mA}$ | 50 | | 150 | |
| | h _{FE2} | $V_{CE} = -1 \ V, \ I_{C} = -1 \ mA$ | 30 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$ | | - 0.1 | - 0.2 | V |
| Transition frequency | f_T | $V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$ | 800 | 1500 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = -5 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 1 | | pF |
| Turn-on time | t _{on} | Refer to the switching time | | 12 | | ns |
| Turn-off time | t _{off} | measurement circuit | | 20 | | ns |
| Storage time | t _{stg} | | | 19 | | ns |

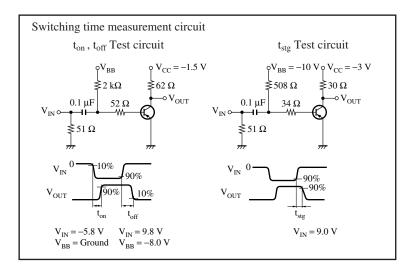
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

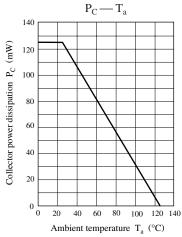
2. *: Rank classification

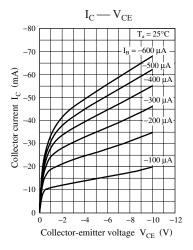
| Rank | Q | R | | |
|---------------|-----------|-----------|--|--|
| $h_{\rm FE1}$ | 50 to 120 | 90 to 150 | | |

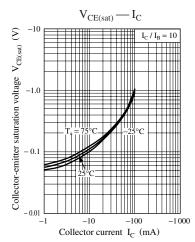
Ranking is not given for any product.

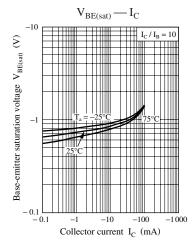
Panasonic

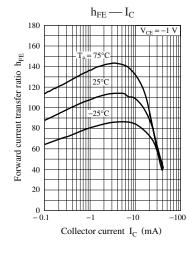


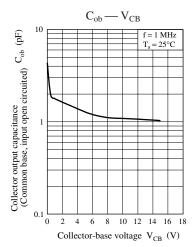












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